Gap opening in the zeroth Landau level of graphene


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(Dated: April 6, 2009)

PACS numbers: 73.43.-f, 73.63.-b, 71.70.Di

In a magnetic field, graphene displays an unconventional Landau-level spectrum of massless chiral Dirac fermions [1, 2, 3, 4]. In particular, a Landau level shared equally between electrons and holes of opposite chirality exists at zero-energy around the charge neutrality point (CNP). Due to the coexistence of carriers with opposite charge, graphene behaves as a compensated semimetal in terms of coexisting electrons and holes in the same spin-split zero-energy Landau level.

We have measured a strong increase of the low-temperature resistivity $\rho_{xx}$ and a zero-value plateau in the Hall conductivity $\sigma_{xy}$ at the charge neutrality point in graphene subjected to high magnetic fields up to 30 T. We explain our results by a simple model involving a field dependent splitting of the lowest Landau level of the order of a few Kelvin, as extracted from activated transport measurements. The model reproduces both the increase in $\rho_{xx}$ and the anomalous $\nu = 0$ plateau in $\sigma_{xy}$ in terms of coexisting electrons and holes in the same spin-split zero-energy Landau level.

Recently, the nature of the CNP in high magnetic fields has attracted considerable theoretical interest (see Ref. [5] and references there in). Experimentally, in the metallic regime, the transport behavior around the CNP can be explained using counter-propagating edge channels [6]. On the other hand, the high-field resistivity at the CNP was shown to diverge strongly, an effect recently attributed to a spontaneous symmetry breaking and an interaction-induced splitting at $v = \pm 1$ state. The existence of this state is proposed to be caused by a spontaneous symmetry breaking at the CNP and an interaction-induced splitting of the two levels resulting from this.

Here we present an experimental study of the transport properties of the zero-energy Landau level in high magnetic fields and at low temperatures. Calculating the conductivities from an increasing magneto-resistance at the CNP and a zero-crossing of the Hall resistance yields a zero minimum in the longitudinal conductivity $\sigma_{xx}$ and a quantized zero-plateau in the Hall conductivity $\sigma_{xy}$. The temperature dependence of the $\sigma_{xx}$-minimum displays an activated behavior. We explain this transition with a simple model involving the opening of a spin-gap (30 K at 30 T) in the zeroth Landau level. We do not observe any indication for a spontaneous symmetry breaking and an interaction-induced splitting at $\nu = \pm 1$ as reported in Refs. 8 and 9 and we tentatively assign this to the relatively larger disorder in our samples from natural graphite.

The monolayer graphene devices (see top left inset Fig. 1a) are deposited on Si/SiO$_2$ substrate using methods as already reported elsewhere [10, 11]. The doped Si acts as a back-gate and allows to adjust the charge-carrier concentration in the graphene film from highly hole-doped to highly electron-doped. Prior to the experiments the devices were annealed at 390 K during several hours removing most of the surface impurities and increasing the low-temperature mobility from $\mu = 0.47$ m$^2$(Vs)$^{-1}$ to $\mu = 1.0$ m$^2$(Vs)$^{-1}$. All measurements were performed with standard AC-techniques at low enough currents to avoid any heating effects.

The Hall conductivity $\sigma_{xy}$ yields a zero minimum in the longitudinal conductivity $\rho_{xx}$ and a zero-zero-crossing of the Hall resistance $\rho_{xy}$. Moving $V_g$ toward zero depopulates the $N = 1$ hole level and moves the Hall resistance to the following plateau, $\rho_{xy} = \hbar / 2 e^2 = 12.9$ k$\Omega$ accompanied by another zero...
in $\rho_{xx}$. Sweeping $V_g$ through zero then depopulates the hole states in the zeroth Landau level and, simultaneously, populates electron states in the same level. $\rho_{xy}$ changes smoothly through zero from its negative quantized value on the hole side to a positive quantized value on the electron side whereas $\rho_{xx}$ moves from a zero on the hole side through a maximum at the CNP to another zero-minimum on the electron side.

In the following we will concentrate on the electronic behavior of graphene around the CNP in high magnetic fields and at low temperatures. Our experimental findings are summarized in Figure 1c. For high magnetic fields ($B > 20$ T) $\rho_{xx}$ strongly increases from a few tens of kilo-ohms to several mega-ohms when the temperatures is lowered down to 0.4 K (left inset in Fig. 1c). Such a field-induced transition can also be seen in the right inset in Fig. 1c: Whereas the magnetoresistance displays a moderate field dependence for sufficiently high temperatures, it starts to increase strongly for $B > 20$ T for the lowest temperature $T = 0.4$ K.

At zero magnetic field the resistivity at the CNP behaves as can be expected, it increases with decreasing temperature toward $\hbar/4e^2$, as carriers are slightly frozen out.

To gain more insight into the peculiar behavior at the CNP we have calculated the longitudinal conductivity $\sigma_{xx}$ and Hall conductivity $\sigma_{xy}$ from the experimentally measured $\rho_{xx}$ and $\rho_{xy}$ by tensor inversion. Possible artifacts due to admixtures of $\rho_{xx}$ on $\rho_{xy}$ and vice versa, caused by contact misalignment and inhomogeneities, were removed, by symmetrizing all measured resistances for positive and negative magnetic fields.

Fig. 2a shows the two components of the conductivity tensor at $B = 30$ T. At low temperatures, the Hall conductivity $\sigma_{xy}$ develops an additional, clearly pronounced, zero-value quantum Hall plateau around the CNP and the longitudinal conductivity $\sigma_{xx}$ displays a thermally activated minimum. Both features are an immediate consequence of the strongly increasing $\rho_{xx}$ at the CNP.

Both the minimum in $\sigma_{xx}$ and the zero-value plateau in $\sigma_{xy}$ at the CNP disappear at elevated temperatures (Fig. 2a) pointing toward an activated transport behavior. Indeed, when plotting $\sigma_{xx}$ in an Arrhenius plot...
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Landau level, with a free-electron $g$-factor $g = 2$ [8]
($\mu_B$ the Bohr magneton). The slightly higher slope of
the experimentally measured gap may be explained by a
sharpening of the zeroth Landau level (i.e. a reduction of
$\Gamma_0$) with increasing field [16], or, alternatively by a slight
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The density of states of graphene in a magnetic field con­
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with a degeneracy of $2eB/h$ for the individual electron
and hole state of the zeroth Landau level and $4eB/h$ for the
higher levels. The zeroth level is relatively sharp [16]
whereas the higher levels are considerably broadened by,
amongst others, random fluctuations of the perpen­
dicular magnetic field caused by the rippled surface of
graphene [17, 18, 19]. Electrons and holes in the center of
the Landau levels are extended (shaded areas) whereas
they are localized in the Landau level tails (filled areas).

With this simple model-density-of-states one can
straightforwardly calculate the longitudinal conductivity
$\sigma_{xx}$ (Fig. 3b) by means of a Kubo-Greenwood formal­
ism [20, 21] and the Hall conductivity $\sigma_{xy}$ (Fig. 3b) by
summing up all the states below the Fermi-energy [22].
The results are shown by the dotted lines in Fig. 3b and
reproduce all the features of a half-integer quantum Hall
effect in graphene [1, 2].

An additional spin-splitting of all the Landau levels
is schematically introduced into the model in the lower
part of Fig. 3a. The splitting is only resolved in the low­
est Landau level, where the level width is already small
enough (20 K). Due to the large broadening of the higher
levels (400 K [16]) it remains unresolved here. Fig. 3b
shows how this splitting nicely reproduces the plateau in
$\sigma_{xy}$ accompanied by a minimum in $\sigma_{xx}$. As soon as the
splitting exceeds the width of the extended states in the
lowest Landau level, the resistivity $\rho_{xx}$ at the CNP starts
to increase as a natural consequence of the tensor inver­
sion of the developing minimum in $\sigma_{xx}$ and the quantized
Hall plateau in $\sigma_{xy}$.

The proposed density of states in Fig. 3b, not only
explains the experimentally observed increase in $\rho_{xx}$ at
the CNP but also the behavior of $\rho_{xy}$. In conventional
semiconductors with a gap, $\rho_{xy}$ develops a singularity
around around the CNP when either electrons or holes
are fully depleted. In our graphene samples, however,
$\rho_{xy}$ is moving through zero from the $\nu = -2$ plateau
with $\rho_{xy} = -h/2e^2 = 12.9$ kΩ to the $\nu = +2$ plateau
at $h/2e^2$. This observation implies that electrons and
holes are coexisting both below and above the CNP and
graphene behaves as a compensated semimetal with as
many hole states as electron states occupied at the CNP.

It should be mentioned in this context that Zhang et al.
have observed an additional splitting of the lowest Lan­
dau level in other samples [8, 9] resulting into additional

$$\sigma_{xx} \propto \exp \left( -\Delta_0/kT \right),$$

we can reasonably fit the data with a single Arrhenius ex­
ponent, yielding an activation gap $\Delta_0$. For low tempera­
tures, we do no more observe a simple activated behavior
since other transport mechanisms such as variable range
hopping [14, 15] start to play an important role. For the
lowest temperatures ($T < 1$ K), the resistance starts to
diverge strongly, an effect which has been suggested to be
caused by the abrupt transition to an ordered truly insu­
lating state [7] and comes on top of the simple activated
behavior.

We can relate the observed activated behavior to the
opening of a gap in the zeroth Landau level (inset in Fig.
2a), $\Delta = 2\Delta_0$, and, therefore, to a partial lifting of
its four-fold degeneracy. The experimentally determined
field dependence of this gap is shown in Fig. 2c. The
gap only becomes visible for fields above 15 T because
of a finite width $\Gamma_0$ of the split Landau level at zero ener­
gy; linear extrapolation of the experimental data to
zero field yields $\Gamma_0 \approx 30$ K. The linear variation of $\Delta$
with magnetic field is, for example, for a spin-split ze­
roth Landau level in other samples [8, 9] resulting into additional

$$\rho_{xx} = \rho_{xx}' \exp \left( -\Delta_0/kT \right),$$

and

$$\rho_{xx}' = \rho_{xx} \left( 1 - \frac{\Delta_0}{E_f} \right)^{-1},$$

where $\rho_{xx}'$ is the value at zero field and $E_f$ is
the Fermi energy.

For comparison we have plotted the theo­
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$$E/(2e^2\hbar B)^{1/2}$$

FIG. 3. (a) Schematic illustration of the density of states for
electrons (red) and holes (blue) in graphene in a magnetic
field without spin-splitting (top) and including spin splitting
(bottom). The width of the higher Landau levels is in reality
much larger than illustrated (see text). (b) $\sigma_{xx}$ and $\sigma_{xy}$ as
a function of charge carrier concentration for unsplit (dotted
lines) and split (solid line) Landau levels calculated for $B = 30$
T and $T = 1$ K and using $g = 2$. 

$\sigma_{xx} \propto \exp \left( -\Delta_0/kT \right),$
quantum Hall plateaus at $\rho_{xy} = \pm \hbar/\epsilon^2 = \pm 25.8 \, \text{k}\Omega$ and $\nu = \pm 1$ minima in $\rho_{xx}$. To explain these results, the degeneracy of electron and hole states has to be removed by lifting the sublattice degeneracy. In this respect, the absence of $\nu = \pm 1$ state in our and other experiments [6, 7, 16] points to a larger disorder, confirmed by the lower mobility, which prevents symmetry breaking. Therefore, we deal with a symmetric density of states for electrons and holes with two-fold degenerate spin-split levels shared by electrons and holes simultaneously.

An important consequence of our experiments is that the gaps measured are more than an order of magnitude smaller than interaction induced gaps. Indeed, the characteristic energy of electron-electron correlation $I = \epsilon^2/4\pi\epsilon_0\epsilon_r l_B$ (where $l_B = \sqrt{\hbar/eB}$ is the magnetic length and $\epsilon_r \approx 2.5$ is the effective dielectric constant for graphene on silicon dioxide) amounts to about 1400 K at 30 T and exceeds the width of the zero-energy Landau level $\Gamma_0$ by nearly two orders of magnitude. According to a simple Stoner-like theory of quantum Hall ferromagnetism [23] this should result in spontaneous breaking of spin and, possibly, valley degeneracy with the formation of quantum Hall ferromagnetism. Since we do not see any evidences of the spontaneous breaking, the effective Stoner parameter is apparently reduced to the value of order of $\Gamma_0$. Probably the sample mobility is not high enough for the stable appearance of a ferromagnetic phase as proposed in Fig. 1 of Ref. 23. A suppression of the Stoner parameter is also what one would naturally expect for narrow-band itinerant-electron ferromagnets due to so called $T$-matrix renormalization [24, 25]. Unfortunately, for the case of quantum-Hall ferromagnetism a consequent theoretical treatment of the effective Stoner criterion with a controllable small parameter is only possible for the limit of high Landau levels [26, 27] and, admittedly, numerous other theoretical scenarios may be considered (see e.g. Ref. 5 and references therein). Therefore, further theoretical efforts are certainly required to clarify this issue.

In conclusion, we have measured the transport properties of the zeroth Landau level in graphene at low temperatures and high magnetic fields. An increasing longitudinal resistance accompanied by a zero crossing in the Hall resistivity at the CNP leads to a flat plateau in the Hall conductivity together with a thermally activated minimum in the longitudinal conductivity. This behavior can be related to the opening of a Zeeman-gap in the density of states of the zeroth Landau level, which reasonably reproduces the features observed experimentally.

This work is part of the research program of the 'Stichting voor Fundamenteel Onderzoek der Materie (FOM)', which is financially supported by the 'Nederlandse Organisatie voor Wetenschappelijk Onderzoek (NWO)'. It has been supported by EuroMagNET under EU contract RI3-CT-2004-506239, the EPSRC, the Royal Society and the European Research Council (Program 'Ideas', Call: ERC-2007-StG).

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